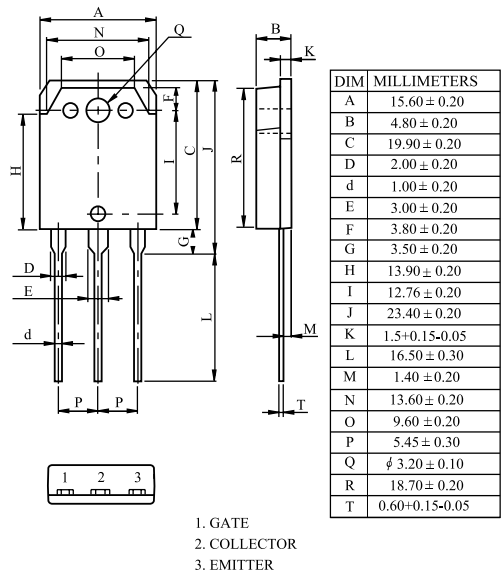
General Description

KEC NPT IGBTs offer low switching losses, high energy efficiency and high avalanche ruggedness for soft switching application such as IH(induction heating), microwave oven, etc.

FEATURES

- High speed switching
- High ruggedness, temperature stable behavior
- Soft current turn-off waveforms
- Extremely enhanced avalanche capability



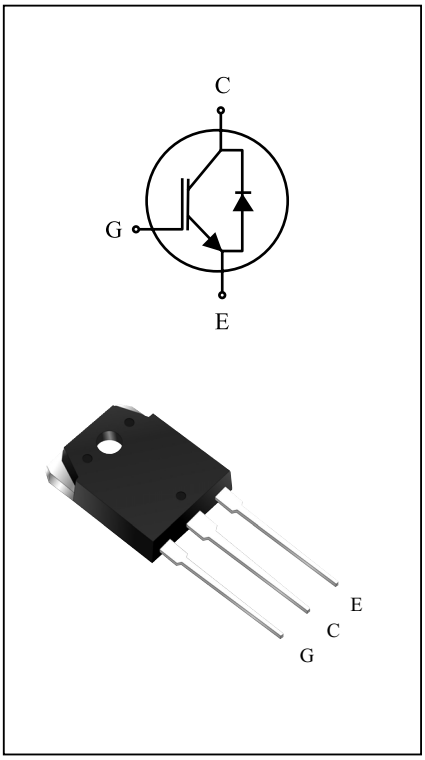
DIM	MILLIMETERS
A	15.60 ± 0.20
B	4.80 ± 0.20
C	19.90 ± 0.20
D	2.00 ± 0.20
d	1.00 ± 0.20
E	3.00 ± 0.20
F	3.80 ± 0.20
G	3.50 ± 0.20
H	13.90 ± 0.20
I	12.76 ± 0.20
J	23.40 ± 0.20
K	1.5+0.15-0.05
L	16.50 ± 0.30
M	1.40 ± 0.20
N	13.60 ± 0.20
O	9.60 ± 0.20
P	5.45 ± 0.30
Q	ϕ 3.20 ± 0.10
R	18.70 ± 0.20
T	0.60+0.15-0.05

TO-3P(N)-E

MAXIMUM RATING (Ta=25℃)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Emitter Voltage		V_{CES}	1350	V
Gate-Emitter Voltage		V_{GES}	±20	V
Collector Current	@Tc=25℃	I_C	50	A
	@Tc=100℃		25	A
Pulsed Collector Current		I_{CM}*	90	A
Diode Continuous Forward Current	@Tc=100℃	I_F	25	A
Diode Maximum Forward Current		I_{FM}	150	A
Maximum Power Dissipation	@Tc=25℃	P_D	220	W
	@Tc=100℃		87	W
Maximum Junction Temperature		T_j	150	℃
Storage Temperature Range		T_{stg}	-55 to + 150	℃

*Repetitive rating : Pulse width limited by max. junction temperature



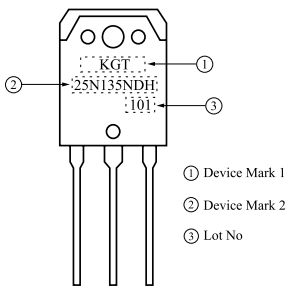
THERMAL CHARACTERISTIC

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Junction to Case (IGBT)	R_{thJC}	0.57	℃/W
Thermal Resistance, Junction to Case (DIODE)	R_{thJC}	2.0	℃/W
Thermal Resistance, Junction to Ambient	R_{thJA}	40	℃/W

ELECTRICAL CHARACTERISTICS (Ta=25℃)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Static						
Collector-Emitter Breakdown Voltage	BV_{CES}	V_{GE}=0V , I_C=1mA	1350	-	-	V
Collector Cut-off Current	I_{CES}	V_{GE}=0V, V_{CE}=1350V	-	-	1.0	mA
Gate Leakage Current	I_{GES}	V_{CE}=0V, V_{GE}=±20V	-	-	±100	nA
Gate Threshold Voltage	$V_{GE(th)}$	V_{GE}=V_{CE}, I_C=25mA	4.5	6.0	7.5	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	V_{GE}=15V, I_C=25A	-	1.85	2.25	V
		V_{GE}=15V, I_C=25A, T_C = 125℃	-	2.15	-	V
		V_{GE}=15V, I_C=50A	-	2.40	-	V
Dynamic						
Total Gate Charge	Q_g	V_{CC}=600V, V_{GE}=15V, I_C= 25A	-	150	-	nC
Gate-Emitter Charge	Q_{ge}		-	20	-	nC
Gate-Collector Charge	Q_{gc}		-	70	-	nC
Turn-On Delay Time	$t_{d(on)}$	V_{CC}=600V, I_C=25A, V_{GE}=15V,R_G=10Ω Inductive Load, T_C = 25℃	-	40	-	ns
Rise Time	t_r		-	25	-	ns
Turn-Off Delay Time	$t_{d(off)}$		-	200	-	ns
Fall Time	t_f		-	150	-	ns
Turn-On Switching Loss	E_{on}		-	3.5	-	mJ
Turn-Off Switching Loss	E_{off}		-	1.2	-	mJ
Total Switching Loss	E_{ts}		-	4.7	-	mJ
Turn-On Delay Time	$t_{d(on)}$	V_{CC}=600V, I_C=25A, V_{GE}=15V, R_G=10Ω Inductive Load, T_C = 125℃	-	45	-	ns
Rise Time	t_r		-	30	-	ns
Turn-Off Delay Time	$t_{d(off)}$		-	210	-	ns
Fall Time	t_f		-	220	-	ns
Turn-On Switching Loss	E_{on}		-	4.0	-	mJ
Turn-Off Switching Loss	E_{off}		-	2.0	-	mJ
Total Switching Loss	E_{ts}		-	6.0	-	mJ
Input Capacitance	C_{ies}	V_{CE}=30V, V_{GE}=0V, f=1MHz	-	2500	-	pF
Ouput Capacitance	C_{oes}		-	100	-	pF
Reverse Transfer Capacitance	C_{res}		-	70	-	pF

Marking



ELECTRICAL CHARACTERISTIC OF DIODE

CHARACTERISTIC	SYMBOL	TEST CONDITION		MIN.	TYP.	MAX.	UNIT
Diode Forward Voltage	V_F	I_F = 25A	T_C=25℃	-	1.8	2.5	V
			T_C=125℃	-	1.9	-	
Diode Reverse Recovery Time	t_{rr}	I_F = 25A di/dt = 200A/ μs	T_C=25℃	-	270	350	ns
			T_C=125℃	-	300	-	
Diode Peak Reverse Recovery Current	I_{rr}		T_C=25℃	-	30	39	A
			T_C=125℃	-	31	-	
Diode Reverse Recovery Charge	Q_{rr}		T_C=25℃	-	3100	4700	nC
			T_C=125℃	-	4650	-	

Fig 1. Saturation Voltage Characteristics

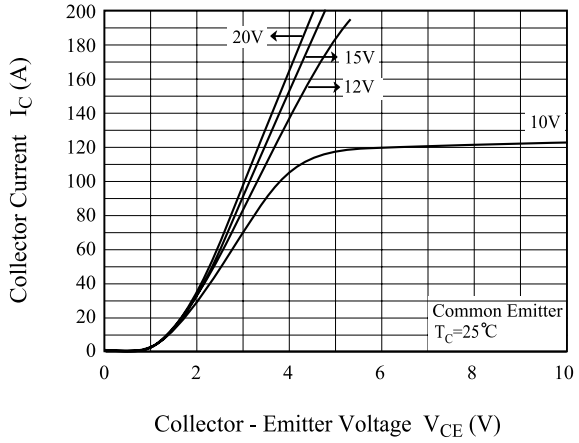


Fig 2. Saturation Voltage Characteristics

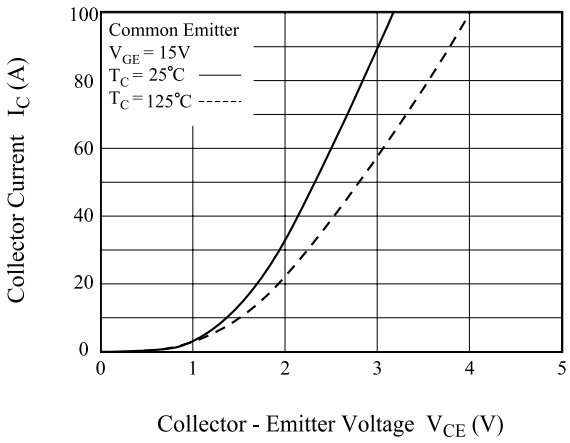


Fig 3. Saturation Voltage vs. Case Temperature

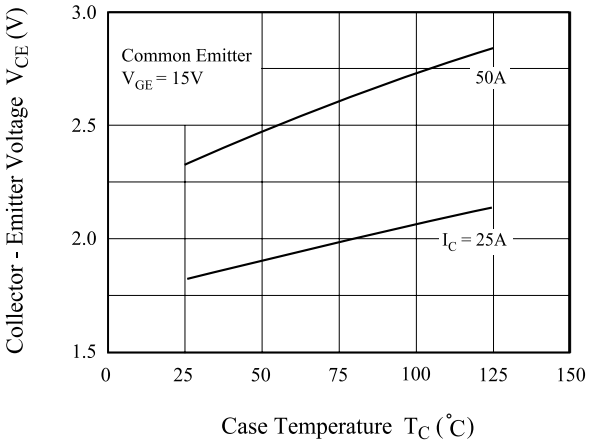


Fig 4. Saturation Voltage vs. V_{GE}

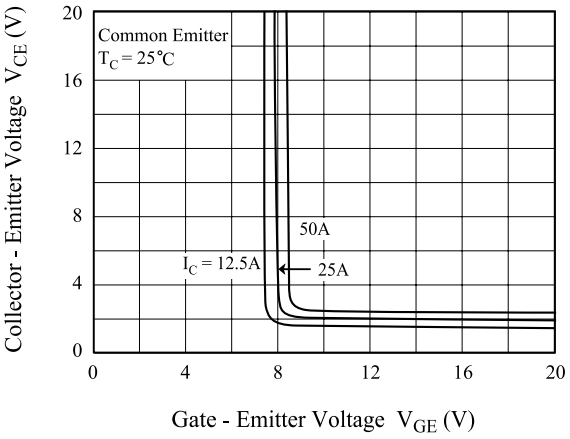


Fig 5. Saturation Voltage vs. V_{GE}

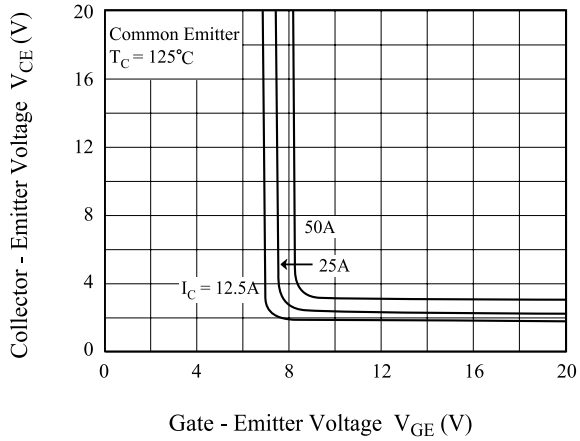


Fig 6. Capacitance Characteristics

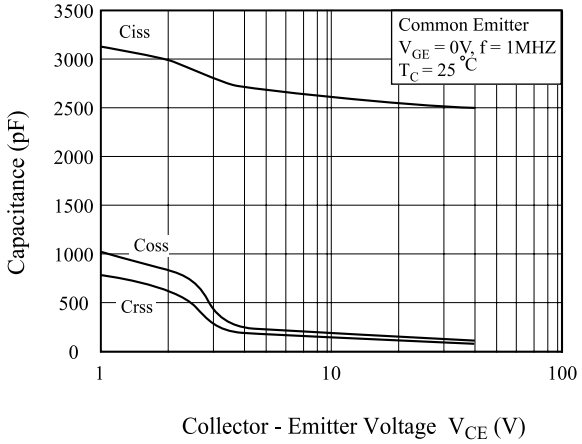


Fig 7. Turn-On Characteristics vs. Gate Resistance

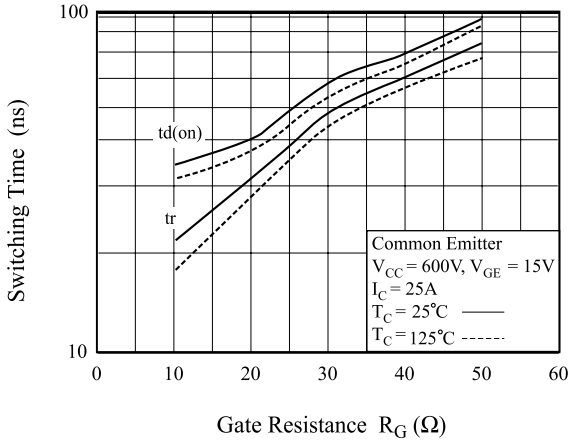


Fig 8. Turn-Off Characteristics vs. Gate Resistance

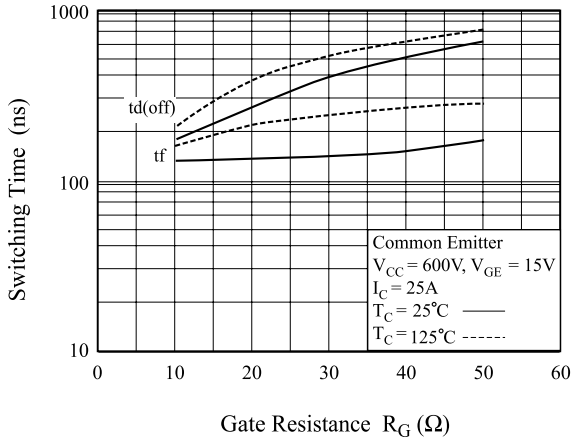


Fig 9. Switching Loss vs. Gate Resistance

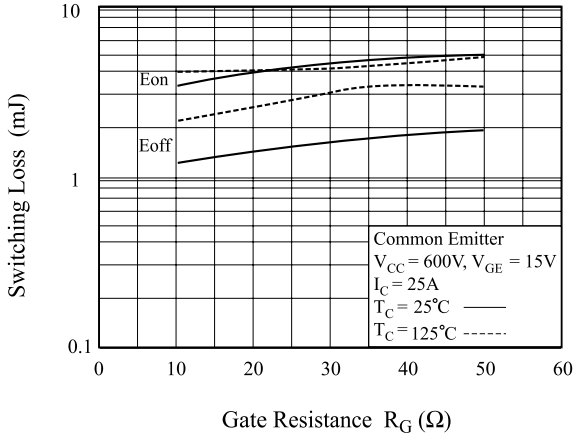


Fig 10. Turn-On Characteristics vs. Collector Current

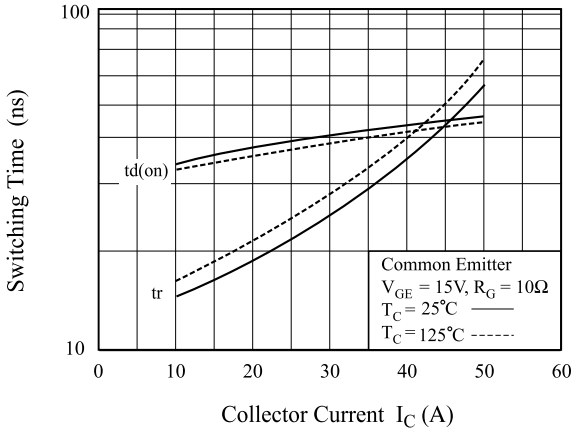


Fig 11. Turn-Off Characteristics vs. Collector Current

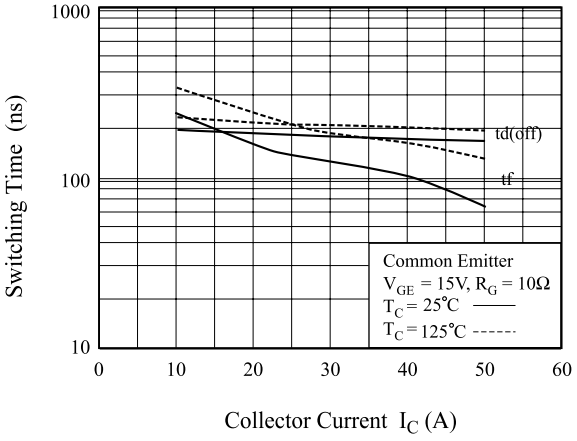


Fig 12. Switching Loss vs. Collector Current

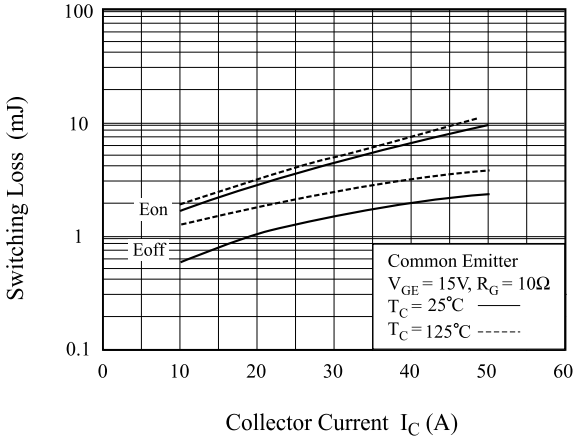


Fig 13. Gate Charge Characteristics

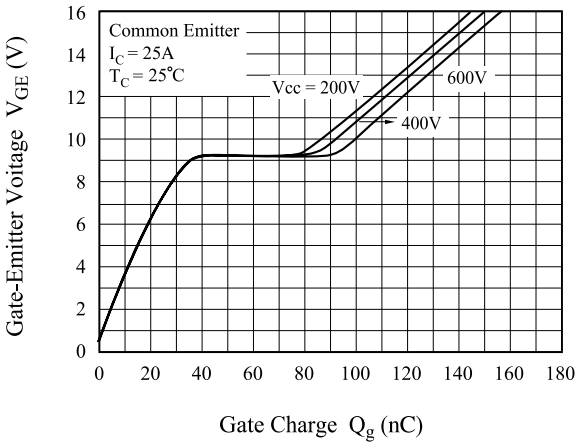


Fig 14. SOA Characteristics

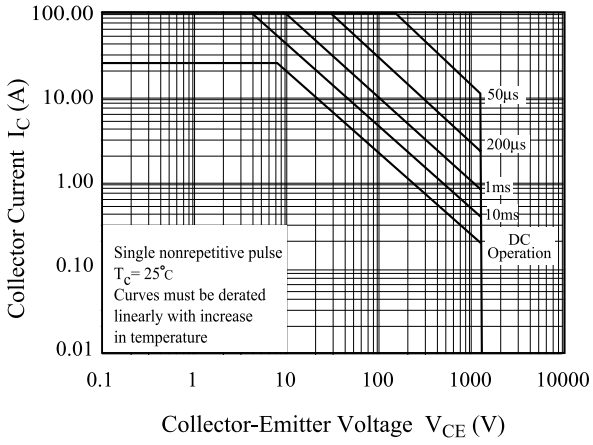


Fig 15. Turn-Off SOA

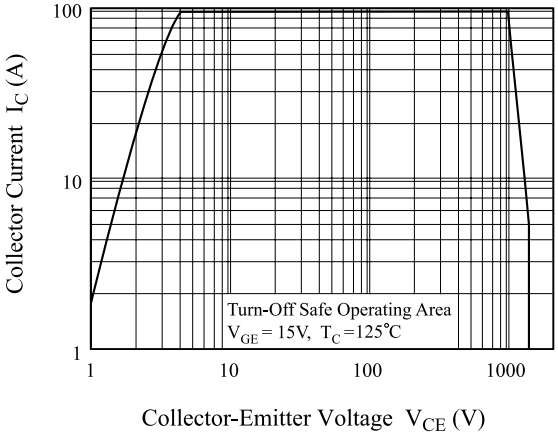


Fig 16. Transient Thermal Impedance of IGBT

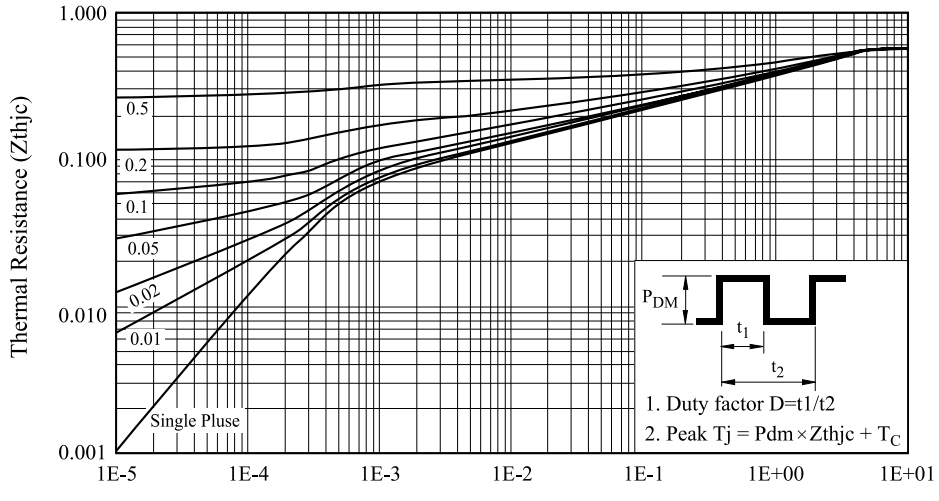


Fig 17. Forward Characteristics

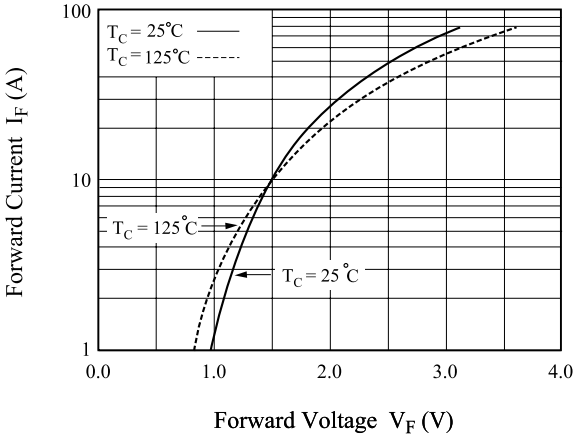


Fig 18. Reverse Recovery Current

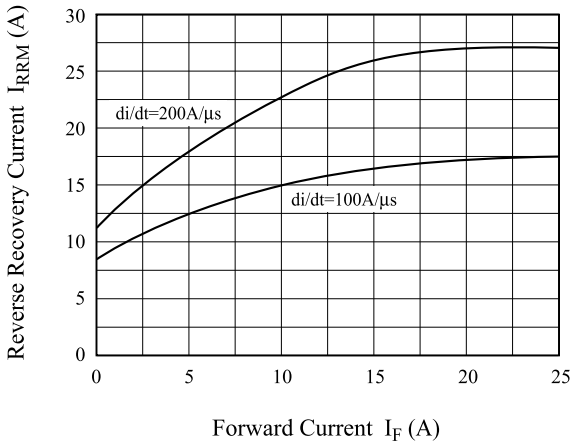


Fig 19. Reverse Recovery Time

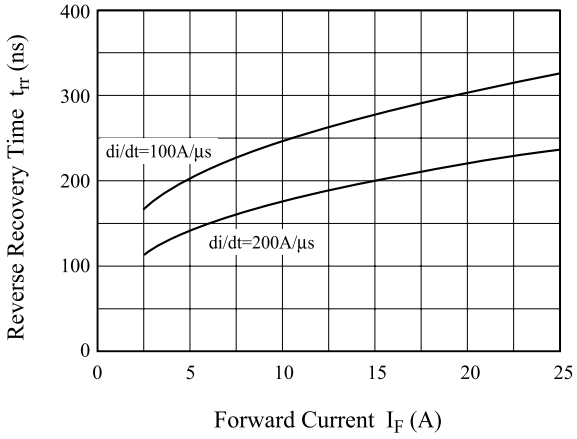


Fig 21. Switching Test Circuit

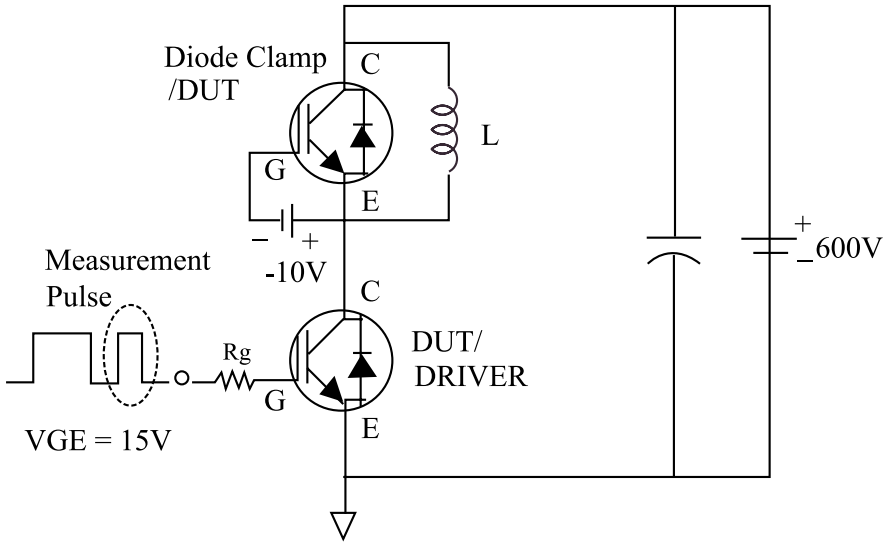
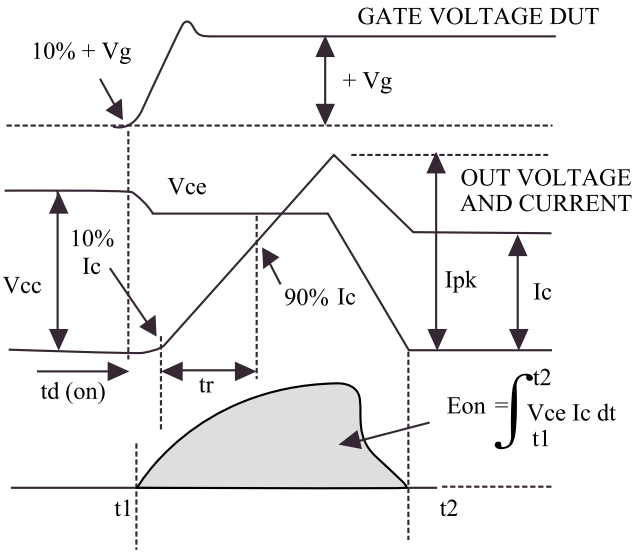


Fig 22. Definition Switching Time & Loss



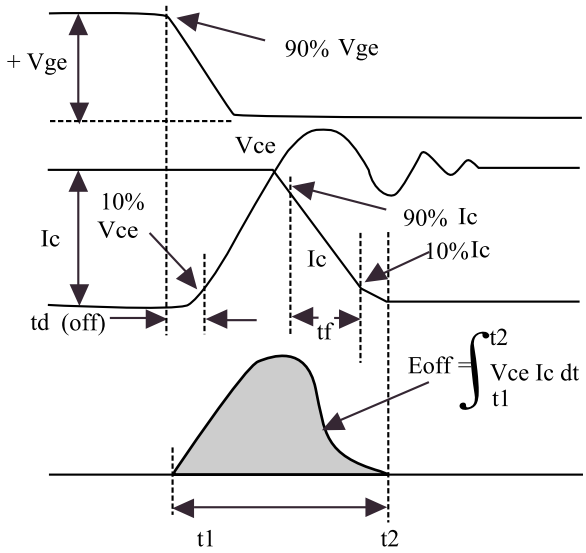


Fig 23. Definition Diode Switching Time